

Group Art Unit: 1765 Examiner: M. Anderson

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to the Commissioner for Patents, Alexandria, VA 22313-1450.

On _	7 October 2005 (DATE OF DEPOSIT)	
	`	,
	Thomas C. Stover	22,531
	NAME OF APPLICANT, ASSIGNEE, OR REG. REP.	
	Les four	
		7 October 2005
	SIGNATURE	DATE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Application of Gerald W. Iseler et al Application Serial No. 10/825,801

Filed: 1 April 2004

For: GROWTH OF UNIFORM CRYSTALS

Honorable Commissioner for Patents Alexandria, VA 22313-1450

Sir:

Declaration Under 37 CFR 1.132

- I, David F. Bliss of Arlington, MA, declare and say that:
- 1. I am one of the inventors in the above identified application filed on 4-1-04.
- 2. I have a Ph.D. in materials science and have worked in the field of Crystal growth in the semi-conductor field for over 20 years.

- 3. Based on this work I can say that low defect crystals are generally grown in a melt by a bottom seeded method. But with a static melt, the distribution of components therein and the properties of the resulting crystals are inherently non-uniform.
- 4. However, when the above melt is electromagnetically stirred, per the invention, crystals of low defect density, uniform distribution of components and of uniform properties result.
- 5. I further declare that the statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true and furthermore that these statements are made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both under section 1001 of Title18 of the United States Code and that such willful false statements could jeopardize the validity of the above application or any patent issuing thereon.

7 October 2005 Date

David F. Bliss